

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1002	(power adj mosfet) same driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:11
S2	26	(power adj mosfet) same driver and (isolation with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S3	2	(power adj mosfet) same driver same (isolation with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S4	16	((power adj mosfet) same driver) and (isolation same oxide same trench)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S5	401	(isolation same oxide same trench same power)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/09 13:25
S6	23849	257/93,374,446,499,564,354-374, 395-399,501,506-527,647,648. ccls. 438/22,207,218,219,48,294, 353,400,225,439,452,427,297, 362,425,439,452,298.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 12:42
S7	18	S6 and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S8	469	(power) same driver and (trench with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 12:42
S9	23865	257/93,374,446,499,564,354-374, 395-399,501,506-527,647,648. ccls. 438/22,207,218,219,48,294, 353,400,225,439,452,427,297, 362,425,439,452,298.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:32

S10	82	S8 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/11 15:32
S11	26	(power adj device) same driver and (trench with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S12	3000	((remove or etch) with portion with oxide) same mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:02
S13	23865	257/93,374,446,499,564,354-374, 395-399,501,506-527,647,648. ccls. 438/22,207,218,219,48,294, 353,400,225,439,452,427,297, 362,425,439,452,298.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 12:42
S14	469	(power) same driver and (trench with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 12:43
S15	417	S12 and S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 12:43
S16	35	S12 and S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S17	10152	((remove or etch) with portion with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:02
S18	57	S17 and S14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:19
S19	4	"6180986"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:31

S20	11	("5602416" "5898196" "6180986" "6198139" "6642577" "6781201"). pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/12 13:32
S21	516	(power) same driver and (trench with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:19
S22	10689	((remove or etch) with portion with oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:19
S23	1	S22 and S21 and @pd>"20050812"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:21
S24	3168	((remove or etch) with portion with oxide) same mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S25	0	S24 and S21 and @pd>"20050812"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S26	0	(power adj device) same driver and (trench with oxide) and @pd>"20050812"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S27	1078	(power adj mosfet) same driver	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S28	24674	257/93,374,446,499,564,354-374, 395-399,501,506-527,647,648. ccls. 438/22,207,218,219,48,294, 353,400,225,439,452,427,297, 362,425,439,452,298.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S29	0	S28 and S27 and @pd>"20050812"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20

S30	0	((power adj mosfet) same driver) and (isolation same oxide same trench) and @pd>"20050812"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S31	0	(power adj mosfet) same driver same (isolation with oxide) and @pd>"20050812"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S32	0	(power adj mosfet) same driver and (isolation with oxide) and @pd>"20050812"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:20
S33	1	(substrate and oxide and layer and uniform and planarizing and polysilicon and epi and trench and isolate).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/01 13:22